Special Issue

Gallium Nitride Sensors

Message from the Guest Editor

Gallium nitride (GaN) and aluminum gallium nitride (AlGaN) devices are attractive candidates for sensing applications in harsh environments due to their wide bandgap, radiation hardness, high-temperature tolerance, and chemical inertness. GaN/AlGaN high-electron-mobility transistors (HEMTs) can be functionalized to fabricate chemical sensors. Schottky barrier diodes (SBDs) and HEMTs can be used as temperature sensors. GaN micro-electro-mechanical system (MEMS) structures have been used for sensing applications. GaN nanowires and quantum dots have been used for chemical sensing. This Special Issue explores the state-of-the-art in using GaN-based devices for sensing applications, including, but not limited to, the examples highlighted above.

Guest Editor

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Sensors is a leading journal devoted to fast publication of the latest achievements of technological developments and scientific research in the huge area of physical, chemical and biochemical sensors, including remote sensing and sensor networks. Both experimental and theoretical papers are published, including all aspects of sensor design, technology, proof of concept and application. Sensors organizes Special Issues devoted to specific sensing areas and applications each year.

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